Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	220022	(metal\$4 NEAR5 oxide\$4 NEAR5 semi\$4conduct\$4) OR \$4MOS	US-PGPUB; USPAT	OR	OFF	2006/03/21 16:43
L2	7597	L1 AND (plasma\$4 NEAR20 nitrid\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/21 16:43
L10	1140	L2 AND (plasma\$4 NEAR20 (oxidiz\$4 OR oxidation\$4))	US-PGPUB; USPAT	OR	OFF	2006/03/21 16:43
L11	227	L10 AND (micro\$1wav\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/21 16:42
L12	188	L11 AND (Ar OR argon\$4 OR helium\$4 OR He)	US-PGPUB; USPAT	OR	OFF	2006/03/21 16:42
L13	6128	((438/770-776,778) or (438/706, 710,719,723,724)).CCLS.	US-PGPUB; USPAT	OR	OFF	2006/03/21 16:42
L15	33	L12 AND L13	US-PGPUB; USPAT	OR	OFF	2006/03/21 16:43
L16	210015	(metal\$4 NEAR5 oxide\$4 NEAR5 semi\$4conduct\$4) OR \$4MOS	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 16:43
L17	314	L16 AND (plasma\$4 NEAR20 nitrid\$4)	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 16:43
L18	21	L17 AND (plasma\$4 NEAR20 (oxidiz\$4 OR oxidation\$4))	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 16:43
S1	1	("20020014666").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/04 15:56
S2	157576	(metal\$4 NEAR5 oxide\$4 NEAR5 semi?conduct\$4) OR MOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/17 09:36
<b>S3</b>	7642	S2 AND (plasma\$4 NEAR20 etch\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 15:59
<b>S4</b>	2119	S3 AND (plasma\$4 NEAR20 nitrid\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 16:39

S5	171	S4 AND (plasma\$4 NEAR20 clean\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 16:00
S6	260	S4 AND (plasma\$4 NEAR20 (oxidiz\$4 OR oxidation\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 16:42
S7	66	S6 AND (micro\$1wav\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 16:42
58	57	S7 AND (Ar OR argon\$4 OR helium\$4 OR He)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 16:42
S12	157576	(metal\$4 NEAR5 oxide\$4 NEAR5 semi?conduct\$4) OR MOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 18:31
S13	7642	S12 AND (plasma\$4 NEAR20 etch\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 18:31
S14	429	S13 AND ((hydrogen OR "H.sub. 2") NEAR20 (Ar OR argon\$4 OR helium\$4 OR He))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 18:32
S15	107	S14 AND (plasma\$4 NEAR20 clean\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 18:32

S16	5637	((438/770-776,778) or (438/706, 710,719,723,724)).CCLS.	US-PGPUB; USPAT	OR	OFF	2006/03/21 16:42
S18	158081	(metal\$4 NEAR5 oxide\$4 NEAR5 semi?conduct\$4) OR MOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/17 11:46
S19	7663	S18 AND (plasma\$4 NEAR20 etch\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/17 11:46
S20	431	S19 AND ((hydrogen OR "H.sub. 2") NEAR20 (Ar OR argon\$4 OR helium\$4 OR He))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR.	OFF	2005/08/17 11:46
S21	107	S20 AND (plasma\$4 NEAR20 clean\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/17 11:46
S22	17	S16 AND S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/17 11:46
S23	219719	(metal\$4 NEAR5 oxide\$4 NEAR5 semi\$4conduct\$4) OR \$4MOS	US-PGPUB; USPAT	OR	OFF	2006/03/17 14:18
S24	7584	S23 AND (plasma\$4 NEAR20 nitrid\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/17 09:40
S25	1137	S24 AND (plasma\$4 NEAR20 (oxidiz\$4 OR oxidation\$4))	US-PGPUB; USPAT	OR	OFF	2006/03/17 09:37
S26	703	S25 AND (Ar OR argon\$4 OR helium\$4 OR He OR Kr)	US-PGPUB; USPAT	OR	OFF	2006/03/17 09:38
S27	191	S26 AND (micro\$1wav\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/17 09:38
S28	34539	S23 AND (nitrid\$4 NEAR20 oxide\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/17 09:40
S29	160	S27 AND (nitrid\$4 NEAR20 oxide\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/17 09:41

S30	17	("20020036320"   "4027320"   "4143388"   "6034418"   "6034430"   "6117749"   "6151240"   "6208030"   "6278138"   "6306734"   "6355580"   "6420764"   "6429496"   "6436748"   "6445043"   "6541393"   "6586792").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/17 09:45
S31	0	S30 AND S26	US-PGPUB;	OR	OFF	2006/03/17 09:45
S35	2	"WO 9833362"	USPAT USOCR;	OR	OFF	2006/03/17 14:00
333	2	WO 7633302	EPO; JPO; DERWENT; IBM_TDB	OK	OFF	2000/03/17 14.00
S36	219719	(metal\$4 NEAR5 oxide\$4 NEAR5 semi\$4conduct\$4) OR \$4MOS	US-PGPUB; USPAT	OR	OFF	2006/03/21 16:39
537	9284	S36 AND oxy\$1nitrid\$4	US-PGPUB; USPAT	OR	OFF	2006/03/17 14:18
S38	795	S37 AND ((high\$4 NEAR5 di\$1electric\$4) NEAR20 oxy\$1nitrid\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/17 14:19
S39	126	S38 AND (plasma\$4 NEAR20 (oxidiz\$4 OR oxidation\$4))	US-PGPUB; USPAT	OR	OFF	2006/03/17 15:11
S40	2355	((wafer\$4 OR silicon\$4) NEAR20 clean\$4) AND ((hydrogen\$4 OR "H.sub.2" OR H2) NEAR20 plasma\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/17 15:12
S41	1951	((wafer\$4 OR silicon\$4) NEAR20 clean\$4) AND (hydrogen\$4 NEAR20 plasma\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/17 15:30
S42	195	((wafer\$4 OR silicon\$4) NEAR20 clean\$4) NEAR20 (hydrogen\$4 NEAR20 plasma\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/17 15:33
S43	43	((wafer\$4 OR silicon\$4) NEAR20 clean\$4) NEAR20 ((hydrogen\$4 AND argon\$4) NEAR20 plasma\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/21 11:32
S44	29	("5660682").URPN.	USPAT	OR	OFF	2006/03/17 16:25
S45	11	(silicon\$4 NEAR20 clean\$4) NEAR20 ((hydrogen\$4 AND argon\$4) NEAR20 plasma\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/17 16:31
S46	31	(silicon\$4 NEAR20 clean\$4) NEAR20 (hydrogen\$4 AND argon\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/17 16:31
S47	612	((wafer\$4 OR silicon\$4) NEAR20 clean\$4) AND ((hydrogen\$4 AND argon\$4) NEAR20 plasma\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/21 11:41

S48	553	S47 AND flow\$4	US-PGPUB; USPAT	OR	OFF	2006/03/21 11:42
S51	534	S48 AND pressur\$4	US-PGPUB; USPAT	OR	OFF	2006/03/21 11:42
S52	542	((wafer\$4 OR silicon\$4) NEAR20 clean\$4) AND (((hydrogen\$4 OR H2 OR "H.sub.2") NEAR20 (argon\$4 OR Ar)) NEAR20 plasma\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/21 11:42
S53	484	S52 AND flow\$4	US-PGPUB; USPAT	OR	OFF	2006/03/21 11:42
S54	461	S53 AND pressur\$4	US-PGPUB; USPAT	OR	OFF	2006/03/21 11:43

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